P-Channel 20-V (D-S) MOSFET

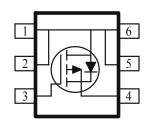
These miniature surface mount MOSFETs utilize High Cell Density process. Low $r_{DS(on)}$ assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are PWMDC-DC converters, power management in portable and battery-powered products such as computers, printers, battery charger, telecommunication power system, and telephones power system.

•	Low r _{DS(on)} Provides Higher Efficiency and
	Extends Battery Life

- Miniature TSOP-6 Surface Mount Package Saves Board Space
- High power and current handling capability

PRODUCT SUMMARY				
$V_{DS}(V)$	$r_{DS(on)}m(\Omega)$	$I_{D}(A)$		
	$56 @ V_{GS} = -4.5V$	-4.9		
-20	$80 @ V_{GS} = -2.5V$	-4.2		
	$150 @ V_{GS} = -1.8V$	-3.1		





ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)					
Parameter			Maximum	Units	
Drain-Source Voltage			-20	V	
Gate-Source Voltage			±12	V	
Continuous Dunin Commut ^a	$T_A=25^{\circ}C$	Ţ	-4.9		
Continuous Drain Current ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	1D	-4.0	A	
Pulsed Drain Current ^b			±20		
Continuous Source Current (Diode Conduction) ^a			-1.7	A	
Decree Disciplation ⁸	$T_A=25^{\circ}C$	D	2.0	W	
Power Dissipation ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	¹ D	1.3	, vv	
Operating Junction and Storage Temperature Range			-55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
M . I	t <= 5 and	D	62.5	°C/W		
Maximum Junction-to-Ambient ^a	$t \le 5 \sec$	$R_{ heta JA}$	110	°C/W		

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Notes

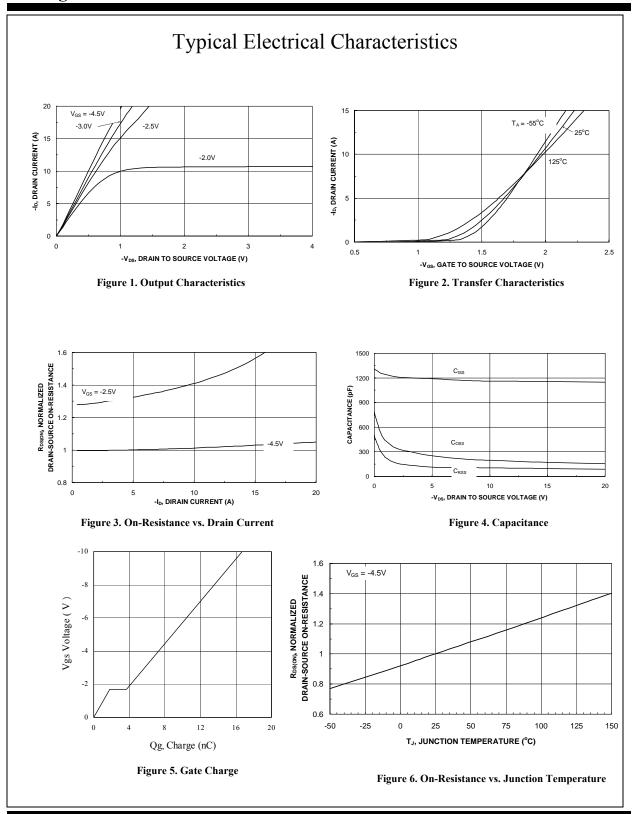
- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Parameter	Causala a l	Test Conditions	Limits			Unit	
r ar ameter	Symbol	Test Conditions	Min	Тур	Max		
Static							
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-0.7				
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA	
Zero Gate Voltage Drain Current	1088	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$			-5		
On-State Drain Current ^A	I _{D(on)}	$V_{DS} = -4.5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-15			A	
		$V_{GS} = -4.5 \text{ V}, I_D = -4.9 \text{ A}$			56		
Drain-Source On-Resistance ^A	$r_{DS(on)}$	$V_{GS} = -2.5 \text{ V}, I_D = -4.2 \text{ A}$			80	$m\Omega$	
		$V_{GS} = -1.8 \text{ V}, I_D = -3.1 \text{ A}$			150		
Forward Tranconductance ^A	$g_{ m fs}$	$V_{DS} = -10 \text{ V}, I_D = -4.9 \text{ A}$		11		S	
Diode Forward Voltage	V_{SD}	$I_S = 1.7 \text{ A}, V_{GS} = 0 \text{ V}$		-0.8		V	
Dynamic ^b							
Total Gate Charge	Qg	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V},$		8			
Gate-Source Charge	Q_{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V},$ $I_{D} = -4.9 \text{ A}$		1.8		nC	
Gate-Drain Charge	Q_{gd}	1 _D = -4.9 A		1.9			
Turn-On Delay Time	$t_{d(on)}$			22			
Rise Time	$t_{\rm r}$	$V_{DD} = -10 \text{ V}, R_L = 6 \Omega, I_D = -1 \text{ A},$		35		nS	
Turn-Off Delay Time	$t_{d(off)}$	VGEN = -4.5 V		45		113	
Fall-Time	$t_{ m f}$			25			

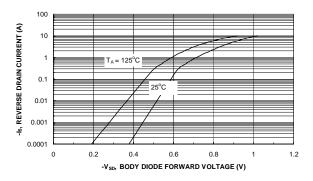
Notes

- a. Pulse test: $PW \le 300us duty cycle \le 2\%$.
- b. Guaranteed by design, not subject to production testing.

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Typical Electrical Characteristics



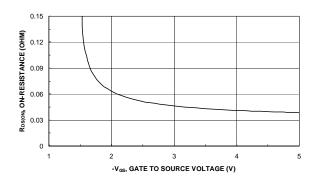


Figure 7. Source-Drain Diode Forward Voltage

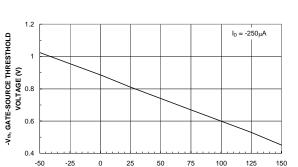


Figure 8. On-Resistance with Gate to Source Voltage

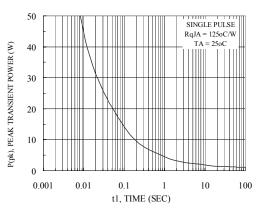


Figure 9. Vth Gate to Source Voltage Vs Temperature

T_A, AMBIENT TEMPERATURE (°C)

Figure 10. Single Pulse Maximum Power Dissipation

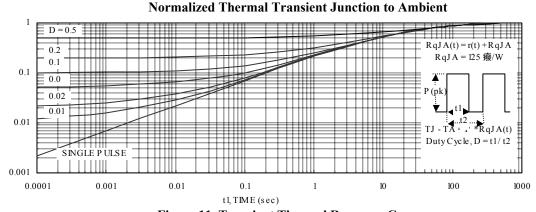
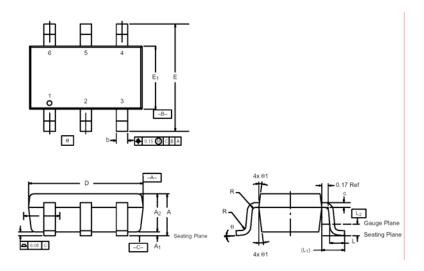


Figure 11. Transient Thermal Response Curve

Package Information

TSOP-6: 6LEAD



	MILLIMETERS			INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.91	-	1.10	0.036	_	0.043
A ₁	0.01	_	0.10	0.0004	-	0.004
A ₂	0.84	_	1.00	0.033	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
С	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
е	1.00 BSC			0.0394 BSC		
L	0.35	_	0.50	0.014	ı	0.020
L ₁	0.60 Ref				0.024 Ref	
L ₂	0.25 BSC				0.010 BSC	
R	0.10	_	-	0.004	_	_
θ	0°	4°	8°	0°	4°	8°
θ_1	7° Nom			7° Nom		

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